

**Features:**

- Isolated mounting base 4000V~
- Pressure contact technology with Increased power cycling capability
- Space and weight saving

**Typical Applications**

- AC/DC Motor drives
- Various rectifiers
- DC supply for PWM inverter

$V_{DSM}, V_{RSM}$	$V_{DRM}, V_{RRM}$	品名
2700V	2600V	Mx200T260C
2900V	2800V	Mx200T280C
3100V	3000V	Mx200T300C
3300V	3200V	Mx200T320C
3500V	3400V	Mx200T340C
3700V	3600V	Mx200T360C

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	$T_j$ (°C)	VALUE			UNIT
				Min.	Typ.	Max.	
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz Single side cooled, $T_c=85^\circ\text{C}$	125			200	A
$I_{T(RMS)}$	RMS on-state current					314	A
$I_{DRM}$ $I_{RRM}$	Repetitive peak current	at $V_{DRM}$ at $V_{RRM}$	125			40	mA
$I_{TSM}$	Surge on-state current	$V_R=60\%V_{RRM}, t=10\text{ms}$ half sine	125			6	kA
$I^2t$	$I^2t$ for fusing coordination					180	$10^3\text{A}^2\text{s}$
$V_{TO}$	Threshold voltage		125			0.96	V
$r_T$	On-state slope resistance					1.30	$\text{m}\Omega$
$V_{TM}$	Peak on-state voltage	$I_{TM}=600\text{A}$	25			2.10	V
$dv/dt$	Critical rate of rise of off-state voltage	$V_{DM}=67\%V_{DRM}$	125			1000	$\text{V}/\mu\text{s}$
$di/dt$	Critical rate of rise of on-state current	Gate source 1.5A $t_r \leq 0.5\mu\text{s}$ Repetitive	125			200	$\text{A}/\mu\text{s}$
$I_{GT}$	Gate trigger current	$V_A=12\text{V}, I_A=1\text{A}$	25	30		180	mA
$V_{GT}$	Gate trigger voltage			0.8		2.5	V
$I_H$	Holding current			20		150	mA
$V_{GD}$	Non-trigger gate voltage	$V_{DM}=67\%V_{DRM}$	125			0.2	V
$R_{th(j-c)}$	Thermal resistance Junction to case	D.C. Single side cooled per chip				0.12	$^\circ\text{C}/\text{W}$
$R_{th(c-h)}$	Thermal resistance case to heat sink	D.C. Single side cooled per chip				0.04	$^\circ\text{C}/\text{W}$
$V_{iso}$	Isolation voltage	50Hz,R.M.S,t=1min, $I_{iso}$ :1mA(MAX)		4000			V
$F_m$	Terminal connection torque (M8)			10.0		12.0	N·m
	Mounting torque (M6)			4.5		6.0	N·m
$T_{vj}$	Junction temperature			-40		125	°C
$T_{stg}$	Stored temperature			-40		125	°C
$W_t$	Weight				770		g
Outline	M03						

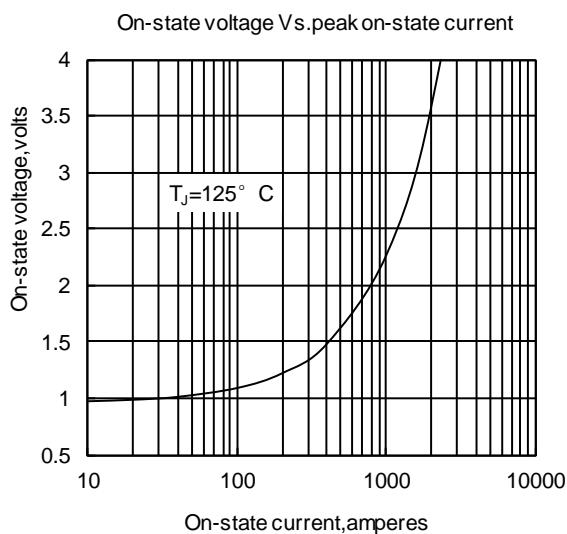


Fig. 1

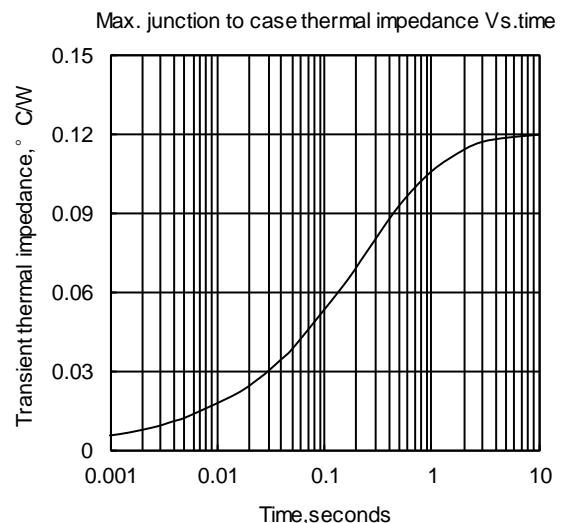


Fig. 2

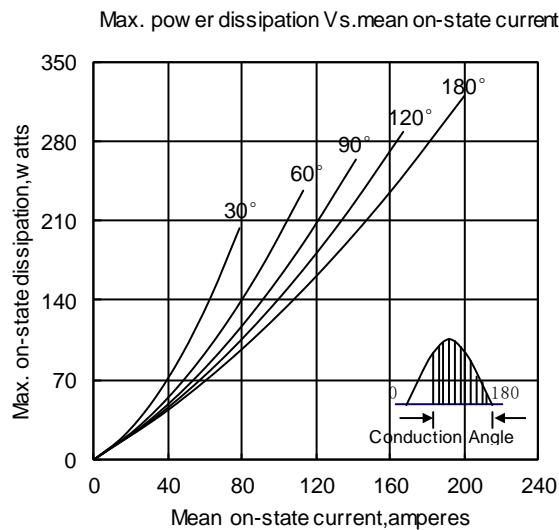


Fig. 3

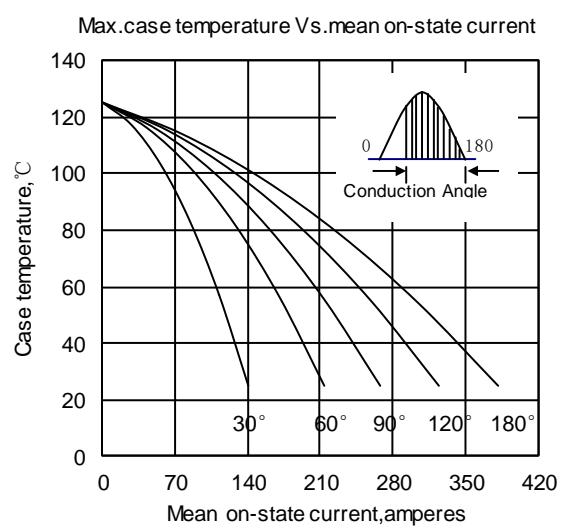


Fig. 4

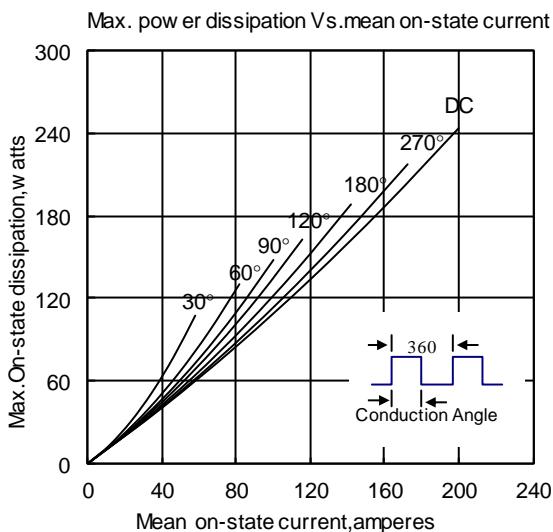


Fig. 5

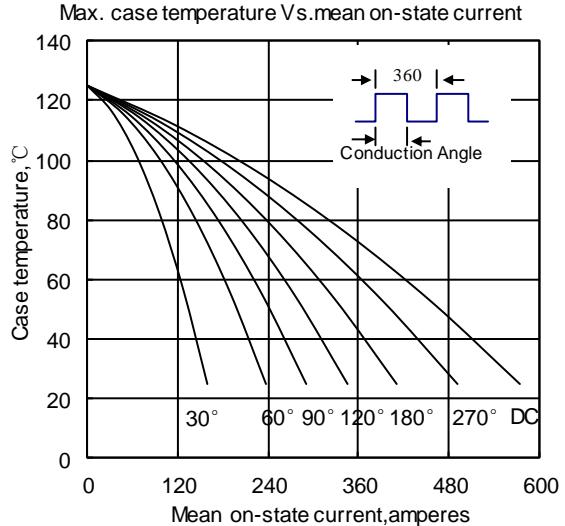


Fig. 6

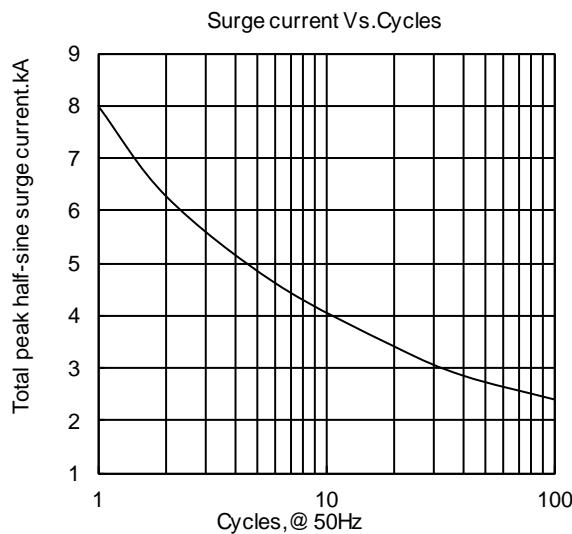


Fig. 7

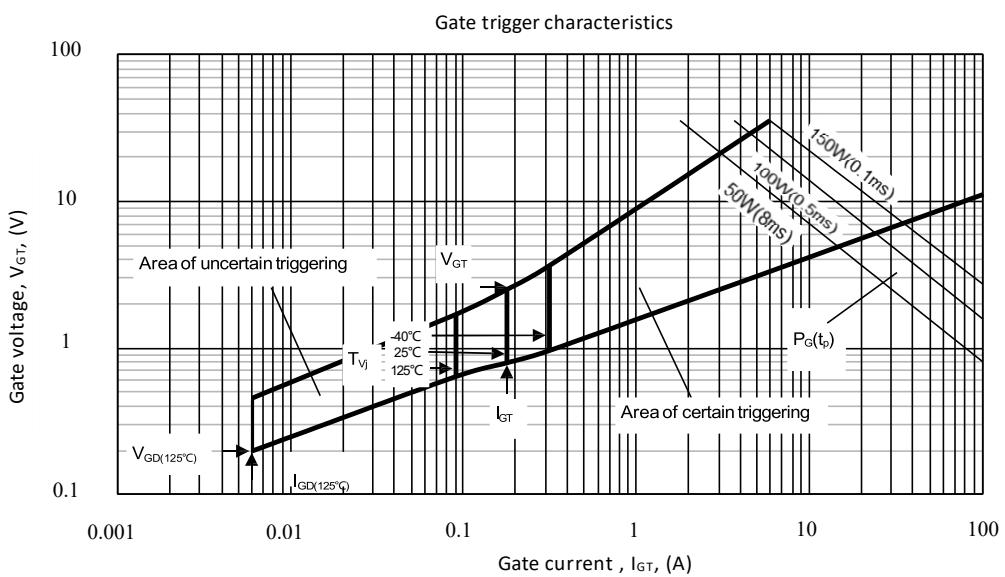
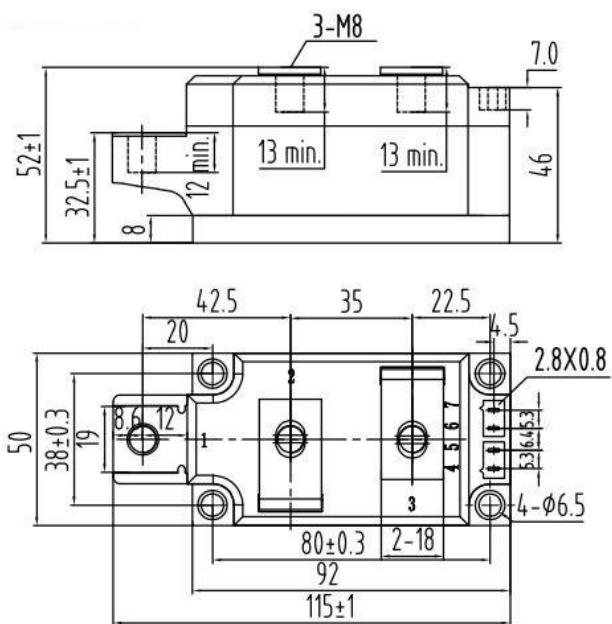


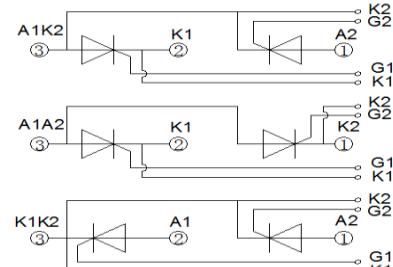
Fig 8



MD200T\*\*C

MR200T\*\*C

MC200T\*\*C



Unmarked dimensional tolerance : ± 0.5mm

NIps reserves the right to change specifications without notice.